5. The method as claimed in claim 3, wherein the adherend has a surface having a height difference of at least 30 μm.

6. The method as claimed in claim 4, wherein the adherend has a surface having a height difference of at least 30 μm.

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7. The method as claimed in claim 3, wherein the adherend is a semiconductor wafer which has a surface having a height difference of at least 30 μm, and which is worked by grinding the back of the semiconductor wafer.

8. The method as claimed in claim 4, wherein the adherend is a semiconductor wafer which has a surface having a height difference of at least 30 μm, and which is worked by grinding the back of the semiconductor wafer.

REMARKS

Claims 1-4 are pending in the present application. Claims 5-8 have been added to particularly claim embodiments of the present pressure sensitive adhesive sheet where the adherend has a surface with a height difference of at least 30 μm and where the adherend is a semiconductor wafer which is worked by grinding the back of the semiconductor wafer. The new claims are supported at page 2, lines 3-18 of the specification. Applicants appreciate the Examiner's indication that the rejection of claims 1-4 under 35 U.S.C. § 103(a) with regard to the tan δ range has been withdrawn.

The present invention is directed to a pressure sensitive adhesive sheet, which includes a substrate and, superimposed thereon, a pressure sensitive adhesive layer. The substrate exhibits a maximum value of dynamic viscoelasticity, as measured by tan δ, of 0.78 to 1.61 at a temperature ranging from –5 to 80°C. The range of tan δ values allows the pressure sensitive adhesive sheet to precisely follow the irregularities, due to bumps and the like, of an adhered wafer surface, enabling smooth back grinding of the adhered surface.